

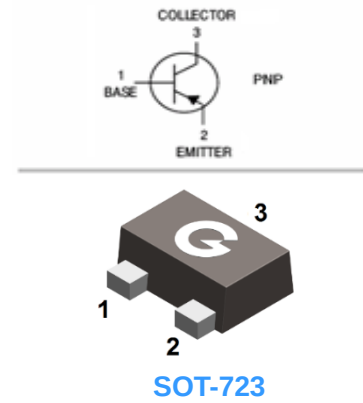
Features

- Epitaxial planar die construction
- Complimentary to MMBT2222AM
- Ultra-small surface mount package

HF

Mechanical Data

- Case: SOT-723
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208



Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
MMBT2907AM	SOT-723	10000 pcs / Tape & Reel	2F

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Breakdown Voltage	V _{CBO}	-60	V
Collector-Emitter Breakdown Voltage	V _{CEO}	-60	V
Emitter-Base Breakdown Voltage	V _{EBO}	-5	V
Collector Current (Continuous)	I _C	-0.6	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation (T _A = 25°C) ^{*1}	P _D	265	mW
Thermal Resistance (Junction-to-Ambient) ^{*1}	R _{θJA}	417	°C/W
Operating junction Temperature	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Note 1: FR-5 = 1.0 X 0.75 X 0.062 in

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}, I_E = 0$	-60	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-60	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}, I_C = 0$	-5	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -50\text{V}, I_E = 0$	-	-	-10	nA
Collector Cut-off Current	I_{CEX}	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -0.5\text{V}$	-	-	-50	nA
Base Cut-off Current	I_{BL}	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -0.5\text{V}$	-	-	-50	nA
DC Current Gain	h_{FE}	$V_{CE} = -10\text{V}, I_C = -0.1\text{mA}$	75	-	-	-
		$V_{CE} = -10\text{V}, I_C = -1\text{mA}$	100	-	-	-
		$V_{CE} = -10\text{V}, I_C = -10\text{mA}$	100	-	-	-
		$V_{CE} = -10\text{V}, I_C = -150\text{mA}$	100	-	300	-
		$V_{CE} = -10\text{V}, I_C = -500\text{mA}$	50	-	-	-
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$	-	-	-1.6	V
		$I_C = -150\text{mA}, I_B = -15\text{mA}$	-	-	-0.4	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$	-	-	-2.6	V
		$I_C = -150\text{mA}, I_B = -15\text{mA}$	-	-	-1.3	V
Transition Frequency	f_T	$I_C = -50\text{mA}, V_{CE} = -20\text{V}$ $f = 100\text{MHz}$	200	-	-	MHz
Collector Output Capacitance	C_{OBO}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$	-	6.5	-	pF
Input Capacitance	C_{IBO}	$V_{EB} = -2\text{V}, I_C = 0, f = 1\text{MHz}$	-	-	8	pF
Delay Time	t_d	$V_{CC} = -30\text{V}, I_C = -150\text{mA}$ $I_{B1} = -15\text{mA}$	-	-	10	ns
Rise Time	t_r		-	-	40	ns
Storage Time	t_s	$V_{CC} = -6\text{V}, I_C = -150\text{mA}$	-	-	225	ns
Fall Time	t_f	$I_{B1} = I_{B2} = -15\text{mA}$	-	-	60	ns

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

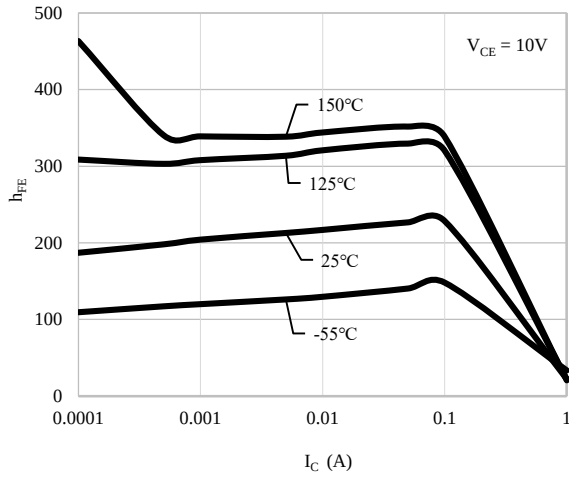


Fig 1 h_{FE} vs. I_C

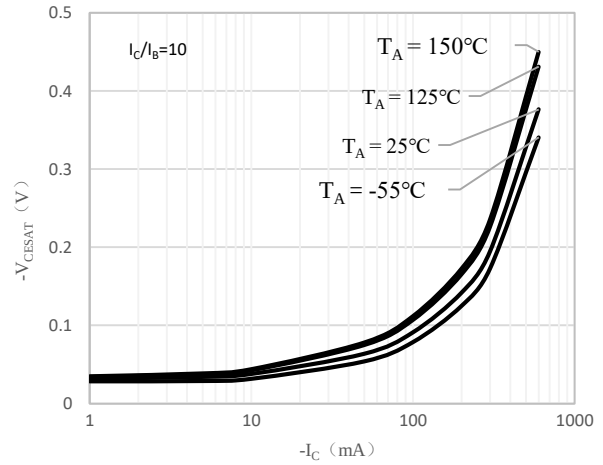


Fig 2 $V_{CE(sat)}$ vs. I_C

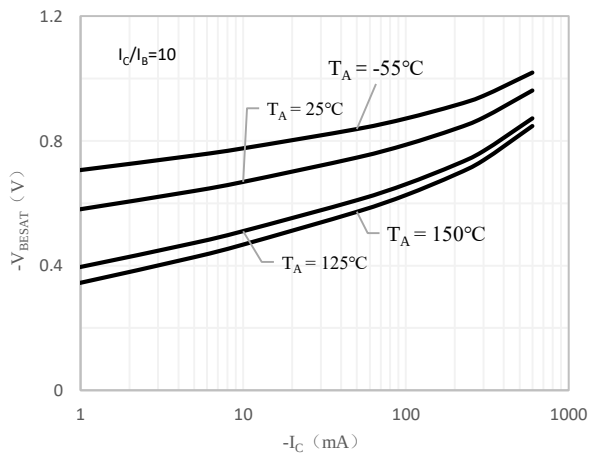


Fig 3 $V_{BE(sat)}$ vs. I_C

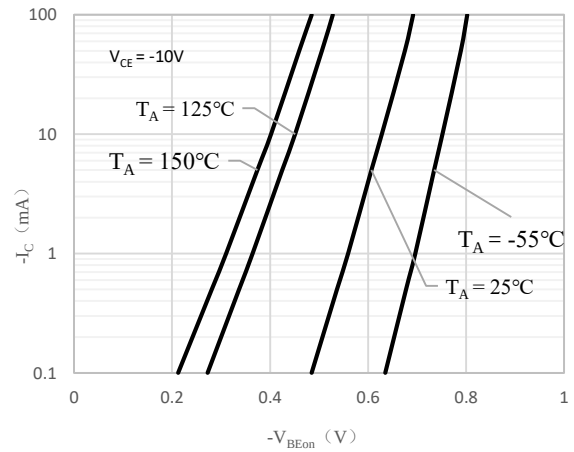
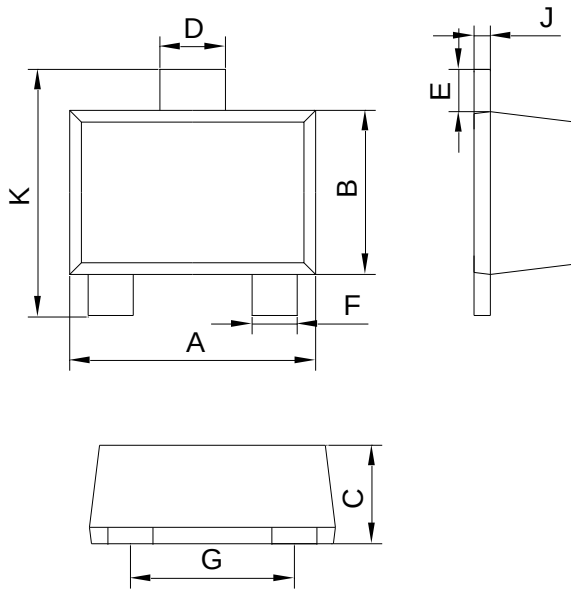


Fig 4 $V_{BE(on)}$ vs. I_C

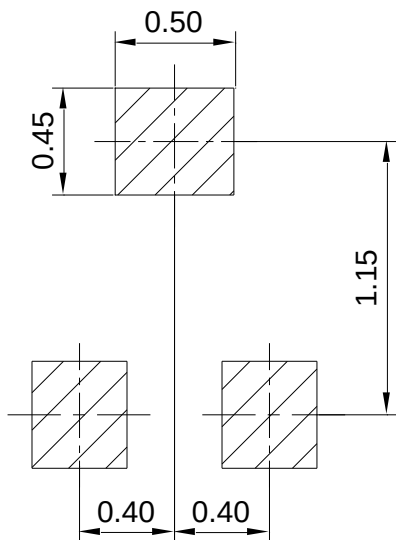
Package Outline Dimensions (Unit: mm)



SOT-723		
Dimension	Min.	Max.
A	1.10	1.30
B	0.70	0.90
C	0.40	0.54
D	0.22	0.42
E	0.10	0.30
F	0.12	0.32
G	0.70	0.90
J	0.08	0.15
K	1.10	1.30

Mounting PAD Layout (Unit: mm)

SOT-723



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